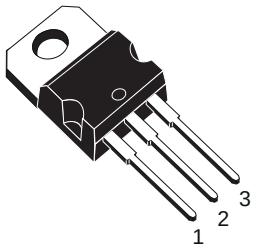
IRF740

N-CHANNEL 400V - 0.46Ω - 10A TO-220
PowerMESH™II MOSFET

TYPE	V_{DSS}	$R_{DS(on)}$	I_D
IRF740	400 V	< 0.55 Ω	10 A

- TYPICAL $R_{DS}(on)$ = 0.46Ω
- EXCEPTIONAL dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- LOW GATE CHARGE
- VERY LOW INTRINSIC CAPACITANCES

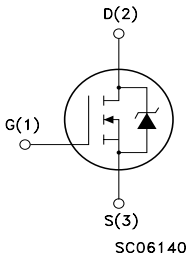


TO-220

DESCRIPTION

The PowerMESH™II is the evolution of the first generation of MESH OVERLAY™. The layout refinements introduced greatly improve the Ron*area figure of merit while keeping the device at the leading edge for what concerns swithing speed, gate charge and ruggedness.

INTERNAL SCHEMATIC DIAGRAM



APPLICATIONS

- HIGH-EFFICIENCY DC-DC CONVERTERS
- UPS AND MOTOR CONTROL

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source Voltage (V_{GS} = 0)	400	V
V_{DGR}	Drain-gate Voltage (R_{GS} = 20 kΩ)	400	V
V_{GS}	Gate- source Voltage	± 20	V
I_D	Drain Current (continuos) at T_C = 25°C	10	A
I_D	Drain Current (continuos) at T_C = 100°C	6.3	A
I_{DM} (●)	Drain Current (pulsed)	40	A
P_{TOT}	Total Dissipation at T_C = 25°C	125	W
	Derating Factor	1.0	W/°C
dv/dt(1)	Peak Diode Recovery voltage slope	4.0	V/ns
T_{stg}	Storage Temperature	– 65 to 150	°C
T_j	Max. Operating Junction Temperature		

(●) Pulse width limited by safe operating area

Note: NEW DATASHEET ACCORDING TO PCN DSG/CT/2C14. SPECIAL MARKING: IRF740 @

(1)I_{SD} ≤10A, di/dt ≤120A/µs, $V_{DD} \le V_{(BR)DSS}$, $T_j \le T_{JMAX}$.

THERMAL DATA

Rthj-case	Thermal Resistance Junction-case Max	1	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	62.5	°C/W
T_l	Maximum Lead Temperature For Soldering Purpose	300	°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max)	10	A
E_{AS}	Single Pulse Avalanche Energy (starting T_j = 25 °C, $I_D = I_{AR}$, V_{DD} = 50 V)	520	mJ

ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	I_D = 250 µA, V_{GS} = 0	400			V
I_{DSS}	Zero Gate Voltage Drain Current (V_{GS} = 0)	V_{DS} = Max Rating			1	µA
		V_{DS} = Max Rating, T_C = 125 °C			50	µA
I_{GSS}	Gate-body Leakage Current (V_{DS} = 0)	V_{GS} = ±20V			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, I_D = 250µA	2	3	4	V
$R_{DS(on)}$	Static Drain-source On Resistance	V_{GS} = 10V, I_D = 5.3 A		0.46	0.55	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$, I_D = 6 A		7		S
C_{iss}	Input Capacitance	V_{DS} = 25V, f = 1 MHz, V_{GS} = 0		1259		pF
C_{oss}	Output Capacitance			206		pF
C_{rss}	Reverse Transfer Capacitance			25.6		pF

ELECTRICAL CHARACTERISTICS (CONTINUED)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	V_{DD} = 200V, I_D = 5 A		17		ns
t_r	Rise Time	R_G = 4.7Ω V_{GS} = 10V (see test circuit, Figure 3)		10		ns
Q_g	Total Gate Charge	V_{DD} = 320V, I_D = 10.7 A,		35	43	nC
Q_{gs}	Gate-Source Charge	V_{GS} = 10V		11		nC
Q_{gd}	Gate-Drain Charge			12		nC

SWITCHING OFF

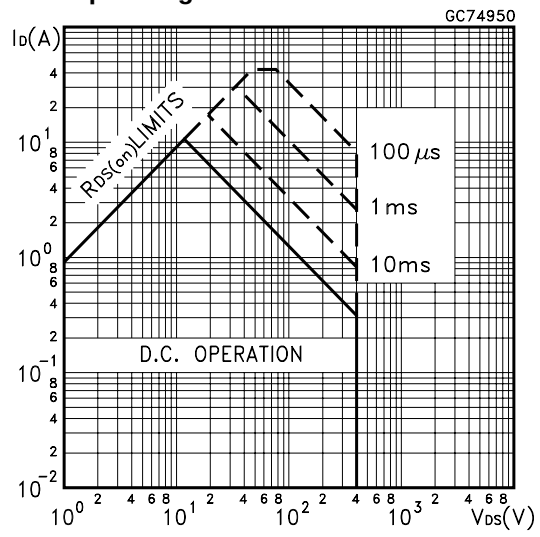
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$	Off-voltage Rise Time	Vclamp = 320V, I_D = 10 A		10		ns
t_f	Fall Time	R_G = 4.7Ω, V_{GS} = 10V		10		ns
t_c	Cross-over Time	(see test circuit, Figure 5)		17		ns

SOURCE DRAIN DIODE

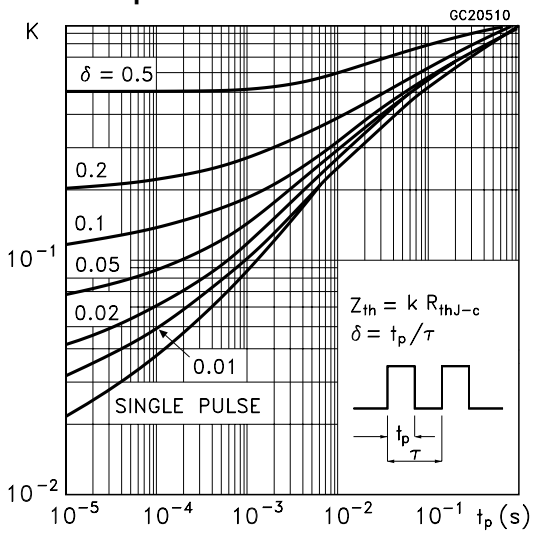
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				10	A
I_{SDM} (2)	Source-drain Current (pulsed)				40	A
V_{SD} (1)	Forward On Voltage	I_{SD} = 10 A, V_{GS} = 0			1.6	V
t_{rr}	Reverse Recovery Time	I_{SD} = 10 A, di/dt = 100A/µs,		370		ns
Q_{rr}	Reverse Recovery Charge	V_{DD} = 100V, T_j = 150°C		3.2		µC
I_{RRM}	Reverse Recovery Current	(see test circuit, Figure 5)		17		A

Note: 1. Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %.
2. Pulse width limited by safe operating area.

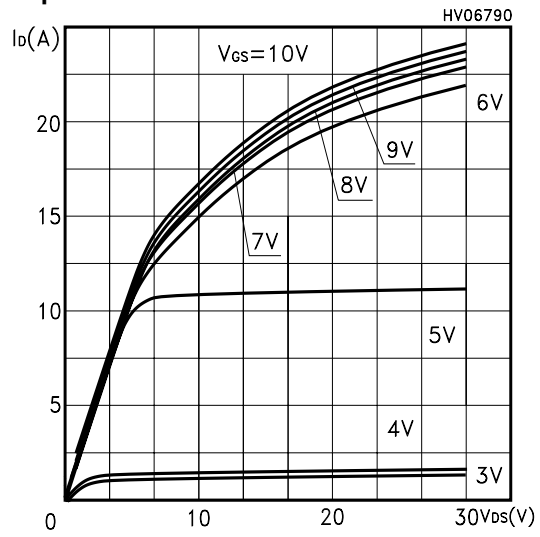
Safe Operating Area



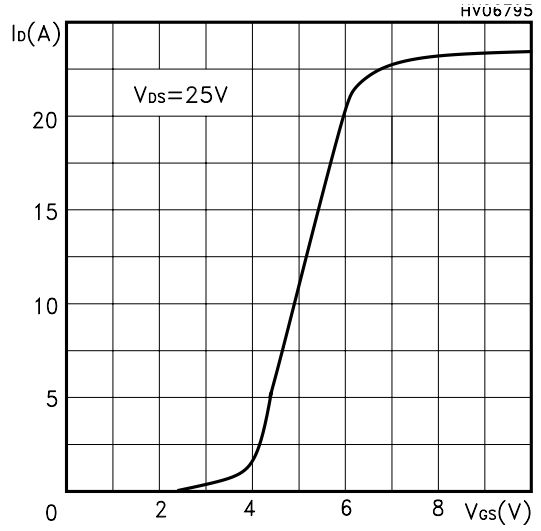
Thermal Impedence



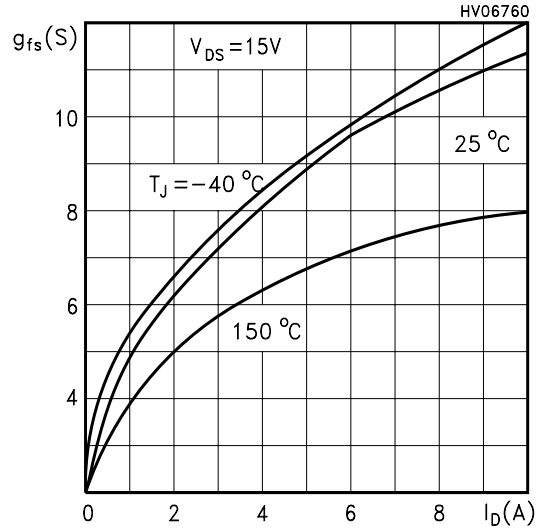
Output Characteristics



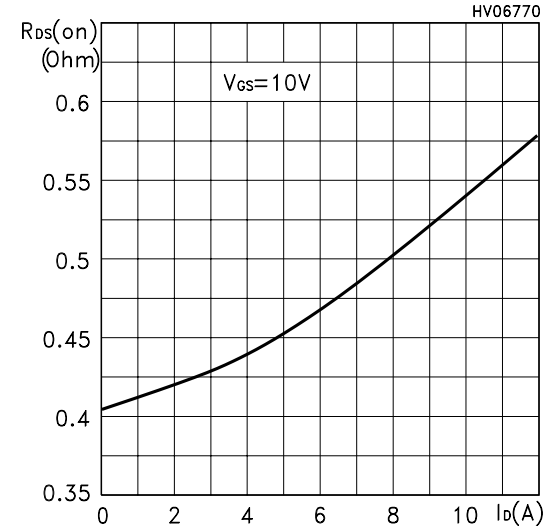
Transfer Characteristics



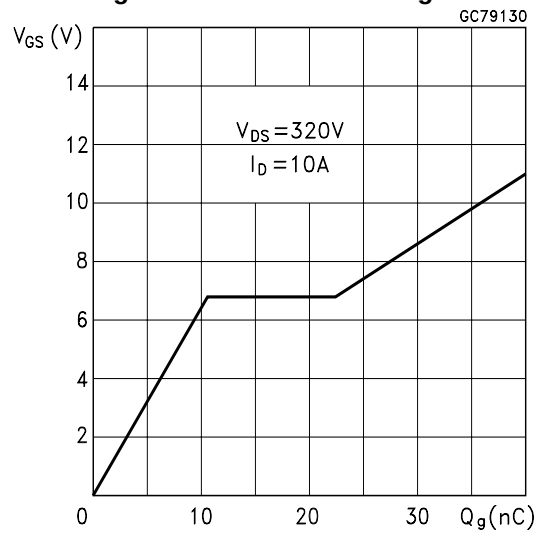
Transconductance



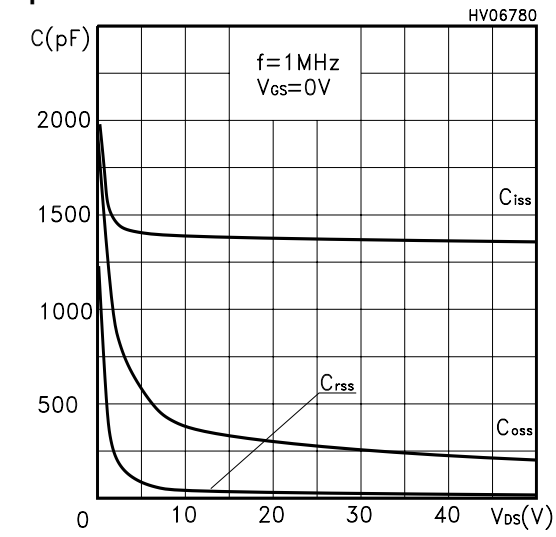
Static Drain-source On Resistance



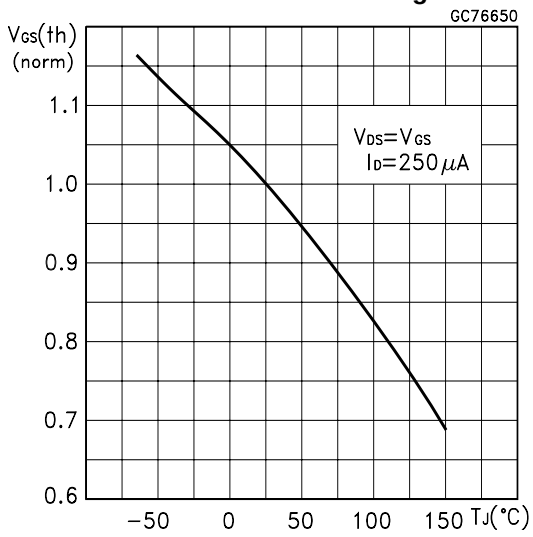
Gate Charge vs Gate-source Voltage



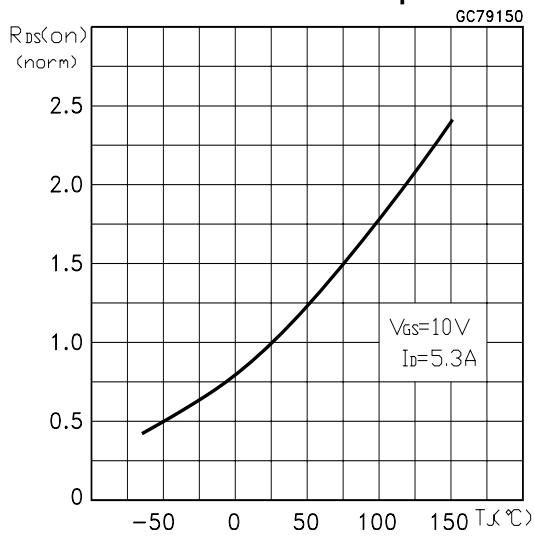
Capacitance Variations



Normalized Gate Thereshold Voltage vs Temp.



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

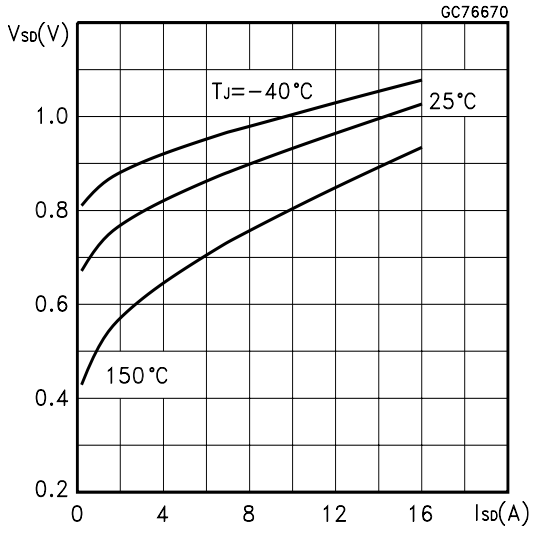


Fig. 1: Unclamped Inductive Load Test Circuit

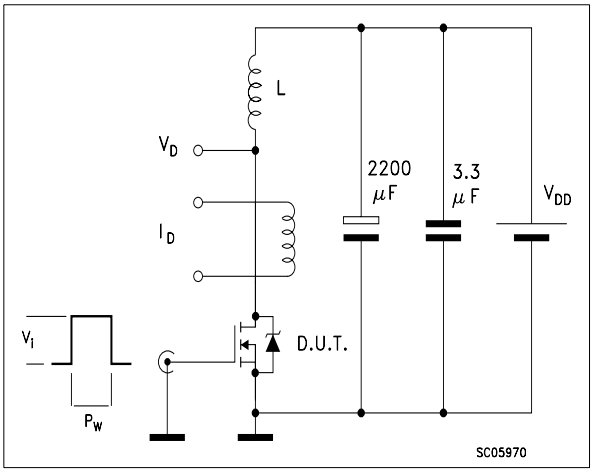


Fig. 2: Unclamped Inductive Waveform

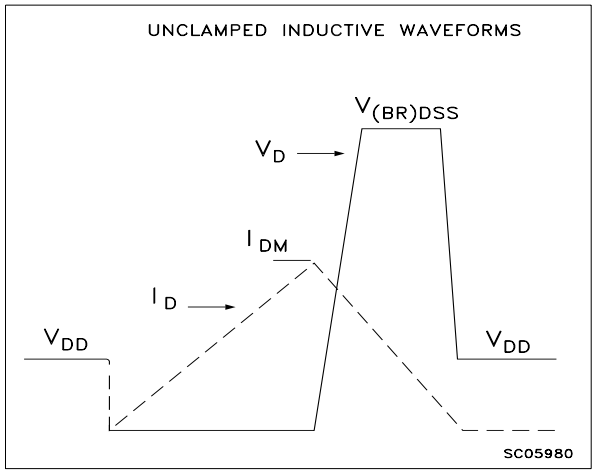


Fig. 3: Switching Times Test Circuit For Resistive Load

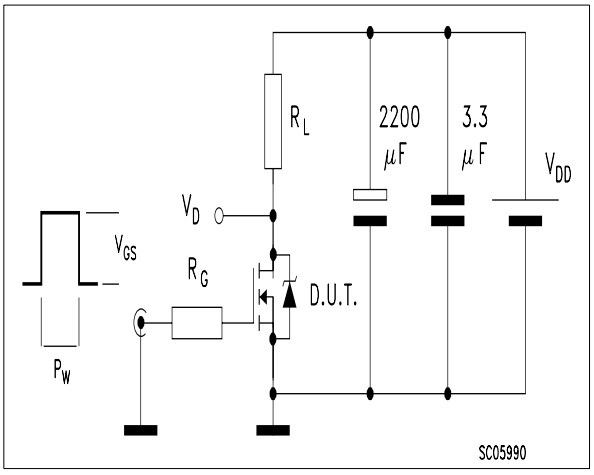


Fig. 4: Gate Charge test Circuit

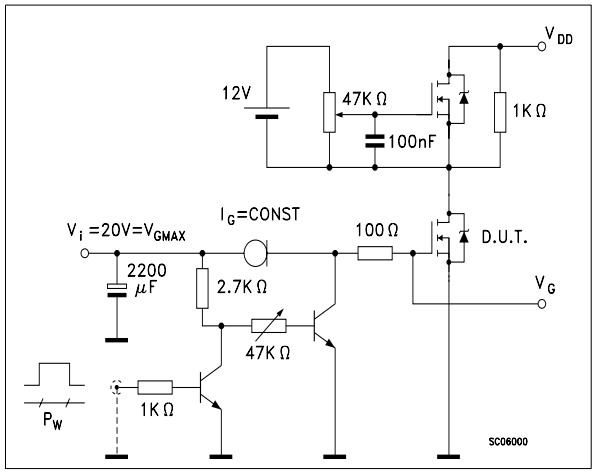
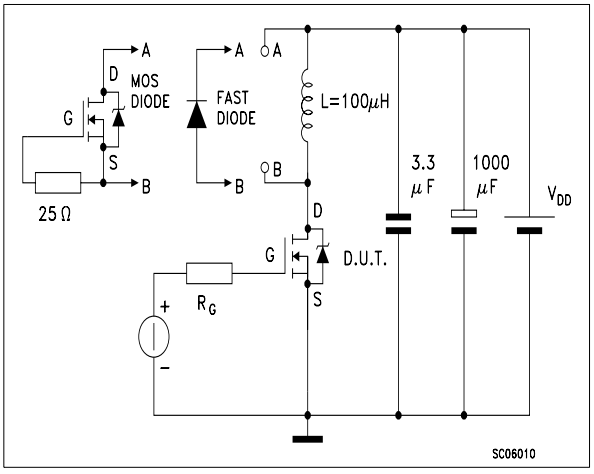


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



TO-220 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116